# UNISONIC TECHNOLOGIES CO., LTD

## UTG25N120LSS2

### Insulated Gate Bipolar Transistor

# 1200V TRENCH GATE FIELD-STOP IGBT

#### ■ DESCRIPTION

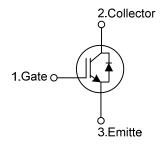
The UTC **UTG25N120LSS2** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

The UTC **UTG25N120LSS2** is suitable for the resonant or soft switching applications.

#### **■** FEATURES

- \* High switching speed
- \* High avalanche ruggedness
- \* Low saturation voltage: V<sub>CE(SAT).Typ.</sub>=1.71V @ I<sub>C</sub>=25A, V<sub>GE</sub>=15V (T<sub>C</sub> =25°C)





#### ORDERING INFORMATION

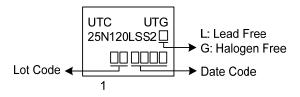
Note: Pin Assignment: G: Gate

Ordering Number		Daakana	Pin Assignment			Daaldaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG25N120LSS2L-T47-T	UTG25N120LSS2G-T47-T	TO-247	G	С	Е	Tube	

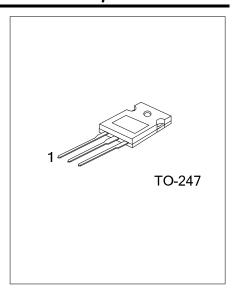
E: Emitter

UTG25N120LSS2G-T47-T
(1)Packing Type
(1) T: Tube
(2)Package Type
(3)Green Package
(3) G: Halogen Free and Lead Free, L: Lead Free

#### MARKING



C: Collector



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#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V	
Gate-Emitter Voltage			±20	V	
Transient Gate-emitter voltage (tp < 5 ms)		$V_{GES}$	±25	V	
Continuous Collector Current	T <sub>C</sub> =25°C	lc	50	Α	
	T <sub>C</sub> =100°C		25	Α	
Collector Current Pulsed (Note 1)		I <sub>CM</sub>	100	Α	
Diada Famuand Cumant	T <sub>C</sub> =25°C		50	Α	
Diode Forward Current	T <sub>C</sub> =100°C	I <sub>F</sub>	25	Α	
Short Circuit Withstand Time					
$V_{\rm GE} = 15 \text{V}, \ V_{\rm CC} \le 200 \text{V}$		t <sub>sc</sub>			
Allowed number of short circuits < 1000			3	μs	
Time between short circuits: ≥1.0s					
T <sub>VJ</sub> = 25°C					
Power Dissipation (T <sub>C</sub> =25°C)		P <sub>D</sub>	260	W	
Operating Junction Temperature		TJ	-40 ~ +150	°C	
Storage Temperature Range		T <sub>STG</sub>	-55 ~ <b>+</b> 150	°C	

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

#### ■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θјς	0.48	°C/W

<sup>2.</sup> Pulse width limited by maximum junction temperature.

### ■ ELECTRICAL CHARACTERISTICS (T<sub>C</sub>=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS			TYP	MAX	UNIT	
Off Characteristics								
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>			1200			V	
Collector Cut-Off Current	I <sub>CES</sub>	V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V				5	μΑ	
G-E Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =±20V				±400	nA	
On Characteristics								
Gate to Emitter Threshold Voltage	$V_{\text{GE(TH)}}$	$I_C$ =250 $\mu$ A, $V_{CE}$ = $V_{GE}$	3.5		6.5	V		
Collector to Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	I <sub>C</sub> =25A, V <sub>GE</sub> =15V	T <sub>C</sub> =25°C		1.71	2.2	V	
			T <sub>C</sub> =125°C		2.1		V	
Dynamic Characteristics							-	
Input Capacitance	CIES			1400		рF		
Output Capacitance	$C_OES$	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1		104		pF		
Reverse Transfer Capacitance	C <sub>RES</sub>	1			57		pF	
Switching Characteristics	_							
Total Gate Charge	$Q_{\mathrm{G}}$				120		nC	
Gate-Emitter Charge	$Q_GE$	V <sub>CE</sub> =520V, I <sub>C</sub> =25A, V <sub>G</sub>		15		nC		
Gate-Collector Charge	$Q_{GC}$			74		nC		
Turn-On Delay Time	t <sub>DON)</sub>			13		ns		
Rise Time	$t_{R}$	V <sub>CC</sub> =400V, I <sub>C</sub> =25A, R <sub>G</sub> =5Ω, V <sub>GE</sub> =0~15V, L=500uH			25		ns	
Turn-Off Delay Time	t <sub>DOFF)</sub>				124		ns	
Fall Time	t <sub>F</sub>				269		ns	
Turn-On Switching Loss	Eon				1.69		mJ	
Turn-Off Switching Loss	E <sub>OFF</sub>	7			2.03		mJ	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Forward Voltage Drop	V <sub>F</sub>	I <sub>F</sub> =25A				3.2	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =25A, dl/dt=100A/μS, V <sub>CC</sub> =400V			54		ns	
Reverse Recovery Charge	Qrr				1145		nC	

#### TEST CIRCUIT AND WAVEFORMS

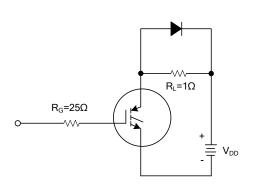


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

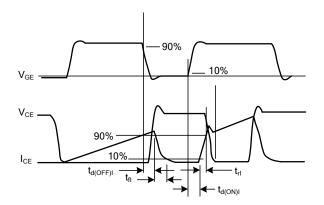


Fig 2. SWITCHING TEST WAVEFORMS

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